

Product data sheet

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TRANSISTOR (PNP)

FEATURES

Low Speed Switching

MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-40	V
V _{CEO}	Collector-Emitter Voltage	-30	V
V _{EBO}	Emitter-Base Voltage	-6	V
lc	Collector Current -Continuous	-3	А
Pc	Collector Power Dissipation	1.25	W
R _{eja}	Thermal Resistance, junction to Ambient	100	°C/W
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55-150	°C

TO-252-2L

1. BASE

2. COLLECTOR

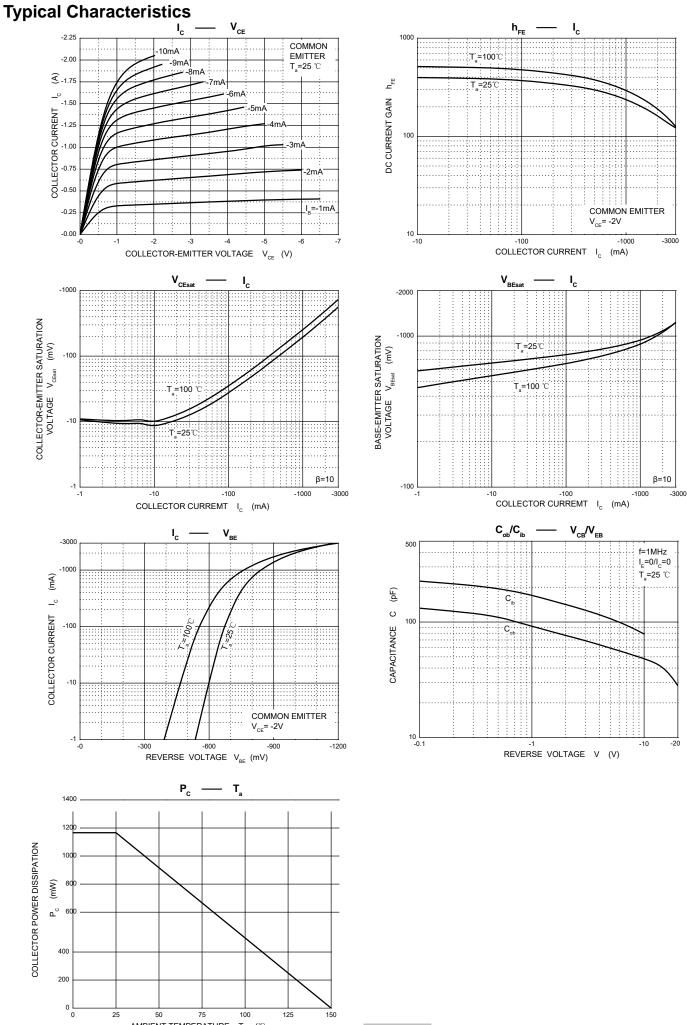
3 .EMITTER

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Тур	Мах	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μΑ ,I _E =0	-40			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = -10mA , I _B =0	-30			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = -100μΑ,I _C =0	-6			V
Collector cut-off current	I _{CBO}	V _{CB} = -40V, I _E =0			-1	μA
Collector cut-off current	I _{CEO}	V _{CE} =-30V, I _B =0			-10	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-6V, I _C =0			-1	μA
DC current gain	h _{FE}	V _{CE} = -2V, I _C = -1A	60		400	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-2A, I _B = -0.2A			- 0.	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-2A, I _B = -0.2A			-1.	V
Transition frequency	f⊤	V _{CE} = -5V, I _C =-0.1A f =10MHz	50	8		MHz



2SB772 HF Compiance

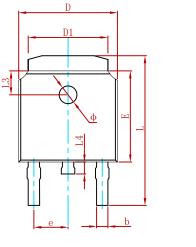


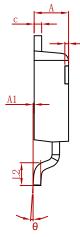
AMBIENT TEMPERATURE T_a (°C Downloaded From Oneyac.com



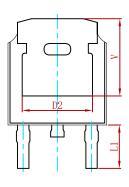


PACKAGE MECHANICAL DATA



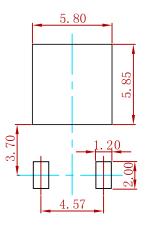


h



Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
Α	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.635	0.770	0.025	0.030	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	4.830 REF.		0.190 REF.		
E	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.712	10.312	0.382	0.406	
L1	2.900 REF.		0.114 REF.		
L2	1.400	1.700	0.055	0.067	
L3	1.600 REF.		0.063 REF.		
L4	0.600	1.000	0.024	0.039	
Φ	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.250	REF.	0.207	REF.	

Suggested Pad Layout



Note:

1.Controlling dimension:in millimeters.

2.General tolerance:± 0.05mm.

3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
2SB772	TO-252	2500





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